

球形汞膜吸附电位溶出法研究痕量铊

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摘要：本文采用球形汞膜吸附电位溶出法对铊进行测定。选择0.1mNaAc, 0.008mKI, 它的线性范围为 0.002~0.01 μgml^{-1} , 搅拌吸附8分钟, 灵敏度为0.0006 μgml^{-1} , 并对吸附剂进行探讨, 实验和理论吻合。

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Determination of trace thallium by the adsorption potential stripping technique
using a spheric mercury electrode

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Abstract: This paper describes determination of trace thallium by the adsorption potential stripping technique, using a spheric mercury film electrode in solution of 0. 1mNaAc , 0. 008mKI. The thallium linear range is 0. 002-0. 01 μgml^{-1} , The sensitivity is 0. 0006 μgml^{-1} after stirring for 8min. theadsorp-tim mechanism is also discussed.

Key words:

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